

2N6298 2N6299 PNP
2N6300 2N6301 NPN

**COMPLEMENTARY SILICON
DARLINGTON POWER TRANSISTORS**



TO-66 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6298 series devices are complementary silicon Darlington power transistors manufactured by the epitaxial base process designed for high gain amplifier and medium speed switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Peak Collector Current
Continuous Base Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	2N6298	2N6299	UNITS
	2N6300	2N6301	
V_{CBO}	60	80	V
V_{CEO}	60	80	V
V_{EBO}		5.0	V
I_C		8.0	A
I_{CM}		16	A
I_B		120	mA
P_D		75	W
T_J, T_{stg}		-65 to +200	$^\circ\text{C}$
θ_{JC}		2.33	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{BE}=1.5\text{V}$		0.5	mA
I_{CEV}	$V_{CE}=\text{Rated } V_{CEO}, V_{BE}=1.5\text{V}, T_C=150^\circ\text{C}$		5.0	mA
I_{CEO}	$V_{CE}=\frac{1}{2}\text{Rated } V_{CEO}$		0.5	mA
I_{EBO}	$V_{EB}=5.0\text{V}$		2.0	mA
BV_{CEO}	$I_C=100\text{mA}$ (2N6298, 2N6300)	60		V
BV_{CEO}	$I_C=100\text{mA}$ (2N6299, 2N6301)	80		V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=16\text{mA}$		2.0	V
$V_{CE(SAT)}$	$I_C=8.0\text{A}, I_B=80\text{mA}$		3.0	V
$V_{BE(SAT)}$	$I_C=8.0\text{A}, I_B=80\text{mA}$		4.0	V
$V_{BE(ON)}$	$V_{CE}=3.0\text{V}, I_C=4.0\text{A}$		2.8	V
h_{FE}	$V_{CE}=3.0\text{V}, I_C=4.0\text{A}$	750	18K	
h_{FE}	$V_{CE}=3.0\text{V}, I_C=8.0\text{A}$	100		
h_{fe}	$V_{CE}=3.0\text{V}, I_C=3.0\text{A}, f=1.0\text{kHz}$	300		
f_T	$V_{CE}=3.0\text{V}, I_C=3.0\text{A}, f=1.0\text{MHz}$	4.0		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (NPN types)		200	pF
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$ (PNP types)		300	pF

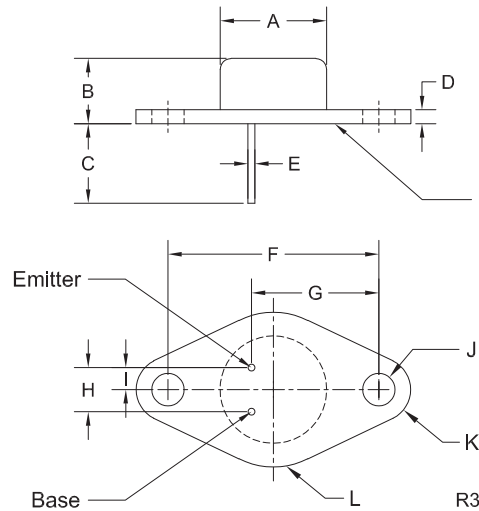
R3 (2-September 2014)

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TO-66 CASE - MECHANICAL OUTLINE



MARKING:
 FULL PART NUMBER

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.470	0.500	11.94	12.70
B	0.250	0.340	6.35	8.64
C	0.360	-	9.14	-
D	0.050	0.075	1.27	1.91
E (DIA)	0.028	0.034	0.71	0.86
F	0.956	0.964	24.28	24.48
G	0.570	0.590	14.48	14.99
H	0.190	0.210	4.83	5.33
I	0.093	0.107	2.36	2.72
J (DIA)	0.142	0.152	3.61	3.86
K (RAD)	0.141		3.58	
L (RAD)	0.345		8.76	

TO-66 (REV:R3)

R3 (2-September 2014)

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- Application notes
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